SUPER FAST RECTIFIERS

VOLTAGE RANGE: 200 --- 600 V CURRENT: 10.0A

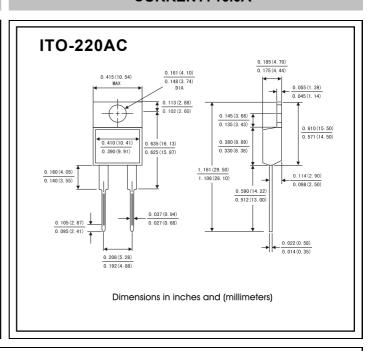
FEATURES

- \Diamond Metal-Semiconductor junction with guard ring
- ♦ Low forward voltage drop,low switching losses
- High surge capability
- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications

MECHANICAL DATA

MIL-STD-750, Method 2026

- Polarity: As marked
- ♦ Weight: 0.08ounces,2.24 grams



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 $^{\circ}$ C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

	Symbols	MUR F 1020	MURF 1040	MURF 1060	Units
Maximum repetitive peak reverse voltage	Vrrm	200	400	600	Volts
Maximum RMS voltage	VRMS	140	280	420	Volts
Maximum DC blocking voltage	VDC	200	400	600	Volts
Maximum average forward rectified current(see Fig.1)	I(AV)	10.0			Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	İFSM	150			Amps
Maximum instantaneous forward voltage at 10.0 A(Note 1)	VF	0.975	1.3	1.7	Volts
Maximum instantaneous reverse current at rated DC blocking	- IR	IR 5 10		10	uA
voltage(Note 1) $T_A = 125^{\circ}C$		500			
Maximum Reverse Recovery Time (Note 2)	Trr	35			ns
Typical thermal resistance (Note 3)	R⊕JC	2.5			°C/W
Operating junction temperature range	TJ	-40 to+150			°C
Storage temperature range	TstG	-40 to+150			°C

NOTE: 1. Pulse test:300us pulse width,1% duty cycle.

2. Thermal resistance junction to ambient

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FIG.1-FORWARD CURRENT DERATING CURVE

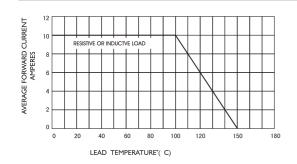


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

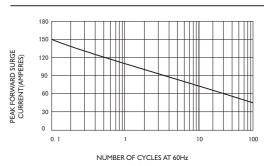


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

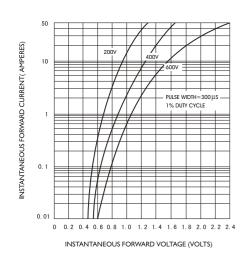


FIG.4-TYPICAL REVERSE CHARACTERISTICS

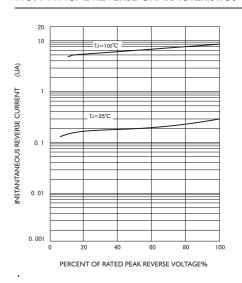


FIG.5-TYPICAL JUNCTION CAPACITANCE

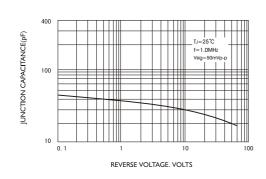
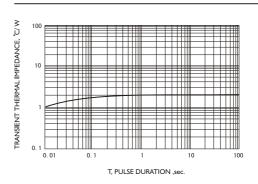


FIG.6-TYPICAL TRANSIENT THERMAL IMPEDANCE



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